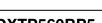


A Product Line of Diodes Incorporated





500V PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR POWERDI[®]5

Features and Benefits

- BV_{CEO} > -500V
- I_C = -150mA Continuous Collector Current
- 47% smaller than SOT223; 60% smaller than TO252 (D-PAK)
- Profile height just 1.1mm for thin application
- $R_{\theta JA}$ efficient giving high P_D rating up to 2.8W
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free, "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: POWERDI[®]5
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.093 grams (approximate)

Applications

- Gate driver
- Startup switch in offline lighting
- Motor Control





С

Pin-Out

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXTP560BP5-13	DXTP560B	13	16	5,000

Notes: 1. No purposefully added lead.

2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com

Marking Information



DXTP560B = Product Type Marking Code DII = Manufacturers' Code Marking K = Factory Designator YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 10 for 2010) WW = Week code (01 - 53)



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic		Symbol	Limit	Unit	
Collector-Base Voltage		V _{CBO}	-500		
Collector-Emitter Voltage		V _{CEO}	-500	V	
Emitter-Base Voltage		V _{EBO}	-7		
Continuous Collector Current	(Note 4)	lc	-150		
Peak Pulse Current		I _{CM}	-500	mA	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit			
	(Note 4)		2.8 22.4			
Power Dissipation Linear Derating Factor	(Note 5)	PD	1.3 10.4	W mW/°C		
	(Note 6)		0.7 5.6	1		
Thermal Resistance, Junction to Ambient	(Note 4) (Note 5) (Note 6)	R _{θJA}	45 96 179	°C/W		
Thermal Resistance, Junction to Lead	(Note 7)	R _{θJL}	14	°C/W		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C			

Notes: 4. For a device surface mounted on 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.

5. Same as note (4), except the device is mounted on 25mm x 25mm 1oz copper.

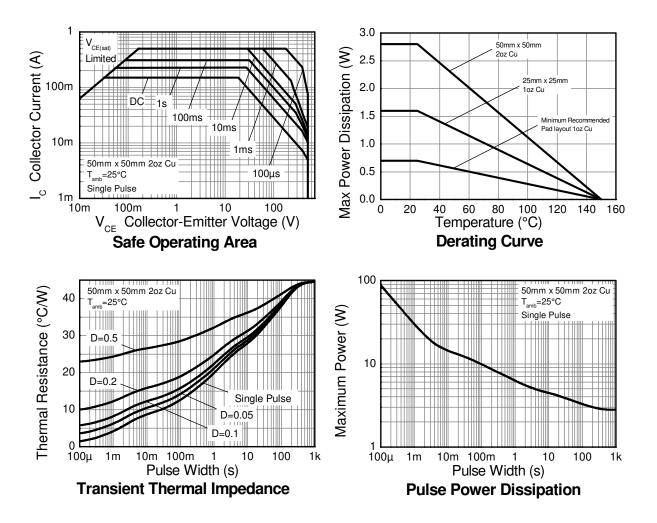
6. Same as note (4), except the device is mounted on a minimum recommended pad layout of 1oz copper.

7. Thermal resistance from junction to solder-point (at the end of the collector lead).





Thermal Characteristics





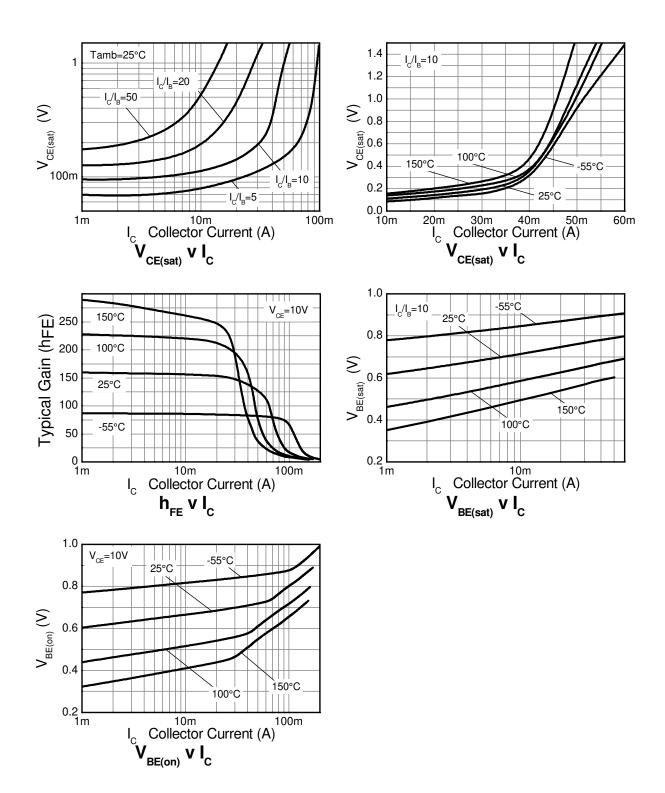
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		-500			V	$I_{\rm C} = -100 \mu {\rm A}$
Collector-Emitter Breakdown Voltage (Note 8)		-500			V	$I_{\rm C} = -10 \mathrm{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7			V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	_	_	-100	nA	V _{CB} = -500V
Collector Cutoff Current	I _{CES}	_	_	-100	nA	V _{CE} = -500V
Emitter Cutoff Current	I _{EBO}	_		-100	nA	V _{EB} = -5.6V
Collector-Emitter Saturation Voltage (Note 8)	N/			-200	mV	I _C = -20mA, I _B = -2mA
Collector-Emiller Saturation Voltage (Note 8)	V _{CE(sat)}			-500	IIIV	$I_{C} = -50mA$, $I_{B} = -10mA$
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}		—	-900	mV	I _C = -50mA, I _B = -10mA
Base-Emitter Turn-On Voltage (Note 8)	V _{BE(on)}			-900	mV	$V_{CE} = -10V, I_{C} = -50mA$
		100		300		$V_{CE} = -10V, I_{C} = -1mA$
DC Current Gain (Note 8)	h _{FE}	80	—	300	—	$V_{CE} = -10V, I_{C} = -50mA$
			15			$V_{CE} = -10V, I_{C} = -100mA$
Transition Frequency	fт	60			MHz	$V_{CE} = -20V, I_{C} = -10mA,$
	-	00				f = 50MHz
Output Capacitance	C _{obo}	—	—	8	pF	V _{CB} = -20V, f = 1MHz
Switching Times	t _{on}		110	—	ns	$V_{CC} = -100V, I_{C} = -50mA,$
	t _{off}	—	1500	—	113	$I_{B1} = 5mA$, $I_{B2} = -10mA$

Notes: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

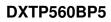


Typical Electrical Characteristics

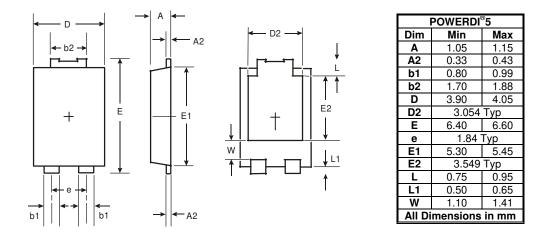


POWERDI is a registered trademark of Diodes Incorporated. DXTP560BP5 5 of 7 Datasheet Number: DS35054 Rev: 1 - 2 www.diodes.com

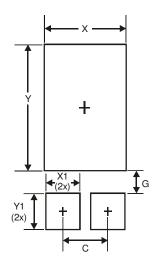




Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
С	1.840
G	0.852
Х	3.360
X1	1.390
Y	4.860
Y1	1.400



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